



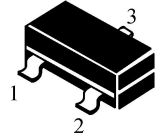
桂林斯壯桂微電子有限責任公司

Guilin Strong Micro-Electronics Co.,Ltd.

GMBTA44(銷售型號 MMBTA44)

SOT-23

- 1. BASE
- 2. EMITTER
- 3. COLLECTOR



FEATURES 特點

NPN High Voltage Transistor

MAXIMUM RATINGS 最大額定值

Characteristic 特性參數	Symbol 符號	Rating 額定值	Unit 單位
Collector-Emitter Voltage 集電極-射極電壓	V_{CEO}	400	V
Collector-Base Voltage 集電極-基極電壓	V_{CBO}	400	V
Emitter-Base Voltage 發射極-基極電壓	V_{EBO}	7	V
Collector Current 集電極電流	I_c	200	mA
Device Dissipation 耗散功率	P_D	225	mW
Junction and Storage Temperature 結溫和儲存溫度	T_J, T_{stg}	-55to+125	°C

ELECTRICAL CHARACTERISTICS 電特性

($T_A=25^{\circ}C$ unless otherwise noted 如無特殊說明，溫度為 $25^{\circ}C$)

Characteristic 特性參數	Symbol 符號	Min 最小值	Max 最大值	Unit 單位
Collector-Emitter Breakdown Voltage 集電極-射極擊穿電壓($I_C=1mA, I_B=0$)	$V_{(BR)CEO}$	400	—	V
Collector-Base Breakdown Voltage 集電極-基極擊穿電壓($I_C=100\mu A, I_E=0$)	$V_{(BR)CBO}$	400	—	V
Emitter-Base Breakdown Voltage 發射極-基極擊穿電壓($I_E=100\mu A, I_C=0$)	$V_{(BR)EBO}$	7	—	V
Collector Cutoff Current 集電極截止電流 ($V_{CB}=300V, I_E=0$)	I_{CBO}	—	500	nA
DC Current Gain 直流電流增益 ($I_C=10mA, V_{CE}=10.0V$)	H_{FE}	40	300	—
Collector-Emitter Saturation Voltage 集電極-發射極飽和壓降 ($I_C=100mA, I_B=10mA$)	$V_{CE(sat)}$	—	0.5	V
Current-Gain-Bandwidth Product 電流增益帶寬乘積 ($I_C=10mA, V_{CE}=20V, f=30MHz$)	f_T	50	—	MHz



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■DEVICE MARKING 打標

GMBTA44(銷售型號 MMBTA44)=3D

■TYPICAL CHARACTERISTIC CURVE

典型特性曲線

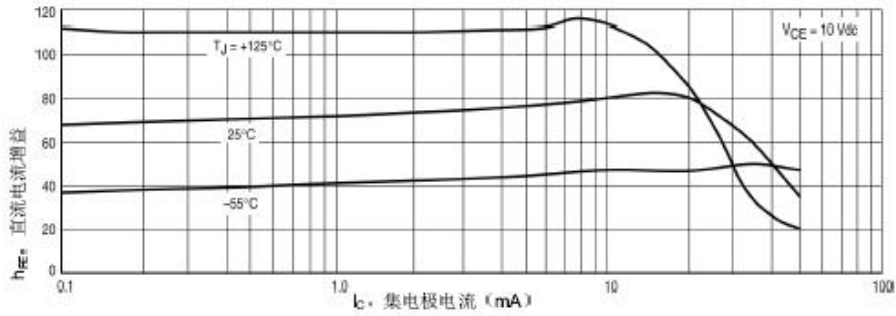


图 1. 直流電流增益

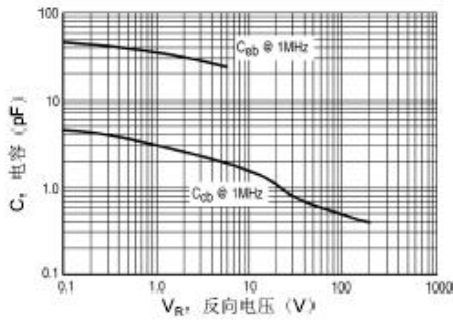


图 2. 電容

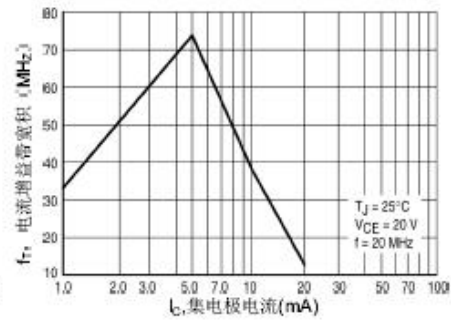


图 3. 電流增益帶寬

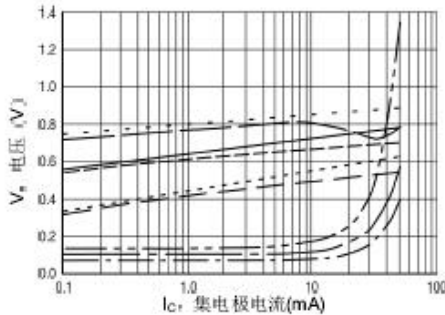


图 4. 導通電壓

- VCE(sat) @ 25°C, IC/IB = 10
- VCE(sat) @ 125°C, IC/IB = 10
- VCE(sat) @ -55°C, IC/IB = 10
- VBE(sat) @ 25°C, IC/IB = 10
- VBE(sat) @ 125°C, IC/IB = 10
- VBE(sat) @ -55°C, IC/IB = 10
- VBE(on) @ 25°C, VCE = 10 V
- VBE(on) @ 125°C, VCE = 10 V
- VBE(on) @ -55°C, VCE = 10 V